

Key Parameters

V_{RRM}	=	2000 V
I_{FAVM}	=	2700 A
I_{FSM}	=	31.0 kA
V_{F0}	=	0.79 V
r_F	=	0.09 mΩ

Avalanche Rectifier Diode

5SDA 27F2002

Doc. No. 5SYA 1127 - 01 Apr-98

Features

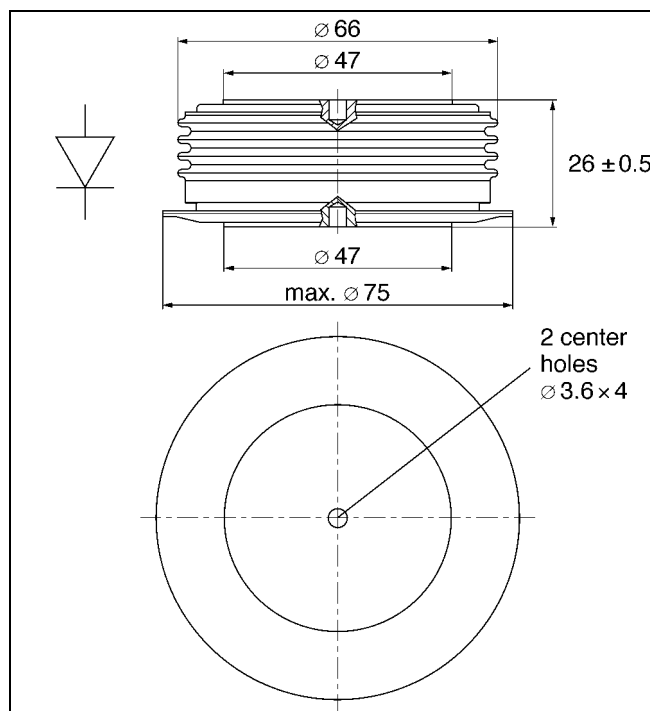
- Optimized for line frequency rectifiers
- Low on-state voltage, narrow V_F -bands for parallel operation
- Self protected against transient overvoltages
- Guaranteed maximum avalanche power dissipation
- Industry standard housing

Blocking

Part number	5SDA 27F2002	5SDA 27F1702	5SDA 27F1402	Condition
V_{RRM}	2000	1700	1400	$f = 50 \text{ Hz}$ $t_P = 10 \text{ ms}$
V_{RSM}	2200	1870	1540	$t_P = 10 \text{ ms}$ $T_j = 160^\circ\text{C}$
I_{RRM}	$\leq 50 \text{ mA}$			V_{RRM} $T_j = 160^\circ\text{C}$
P_{RSM}	$\leq 140 \text{ kW}$			$t_P = 20 \mu\text{s}$ $T_j = 45^\circ\text{C}$
	$\leq 100 \text{ kW}$			$t_P = 20 \mu\text{s}$ $T_j = 160^\circ\text{C}$

Mechanical data

F_M	Mounting force	min.	20 kN
		max.	24 kN
a	Acceleration	Device unclamped	50 m/s ²
		Device clamped	200 m/s ²
m	Weight		0.5 kg
D_s	Surface creepage distance		30 mm
D_a	Air strike distance		20 mm



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Darrah Electric Company
www.darrahelectric.com

ABB Semiconductors AG



On-state

I _{FAVM}	Max. average on-state current	2700 A	Half sine wave, T _C = 85°C	
I _{FRMS}	Max. RMS on-state current	4240 A		
I _{FSM}	Max. peak non-repetitive surge current	31.0 kA	tp =	10 ms
		33.5 kA	tp =	8.3 ms
I ² t	Limiting load integral	4805·10 ³ A ² s	tp =	10 ms
		4680·10 ³ A ² s	tp =	8.3 ms
V _{F0}	Threshold voltage	0.79 V	I _F = 2000 - 6000 A	T _j = 160°C
r _F	Slope resistance	0.09 mΩ		
V _{F min}	On-state voltage	1.05 V	I _F = 4000 A	T _j = 25°C
V _{F max}	On-state voltage	1.20 V		

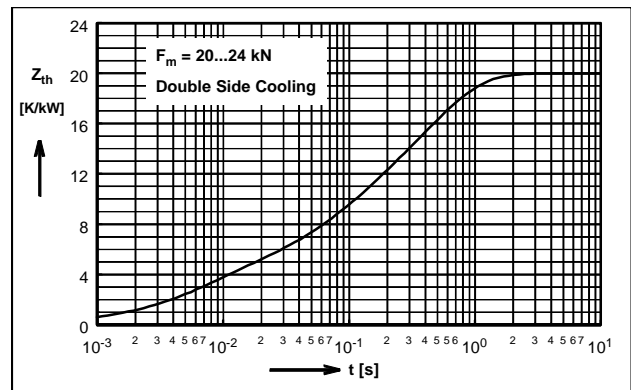
Thermal

T _j	Storage and operating junction temperature range	-40...160°C	
R _{thJC}	Thermal resistance junction to case	40 K/kW	Anode side cooled
		40 K/kW	Cathode side cooled
		20 K/kW	Double side cooled
R _{thCH}	Thermal resistance case to heat sink	10 K/kW	Single side cooled
		5 K/kW	Double side cooled

Analytical function for transient thermal impedance:

$$Z_{thJC}(t) = \sum_{i=1}^4 R_i(1 - e^{-t/\tau_i})$$

i	1	2	3	4
R (K/kW)	11.83	4.26	1.63	2.28
τ _i (s)	0.432	0.071	0.01	0.0054



For a given case temperature T_c at ambient temperature T_a the maximum on-state current can be calculated as follows:

$$I_{FAVM} = \frac{-V_{F0} + \sqrt{(V_{F0})^2 + 4 * f^2 * r_f * P}}{2 * f^2 * r_f}$$

I_{FAVM} (A) P (W) V_{F0} (V) r_f (Ω)
 T_{max} (°C) T_c (°C) T_a (°C)
 R_{thja} (K/kW) R_{thJC} (K/kW)

where P = $\frac{T_{Jmax} - T_C}{R_{thjc}}$ or P = $\frac{T_{Jmax} - T_A}{R_{thja}}$

f² = 1 for DC current
 2.5 for half-sine wave
 3.1 for 120°el., sine
 6 for 60° el., sine

